

# **A Low-Cost Approach to Fabrication of Multinary Compounds for Energy-Related Applications**

**Preprint**

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*To Be Presented at the 12<sup>th</sup> International Conference in  
Ternary and Multinary Compounds  
Hsin-chu, Taiwan  
March 13-17, 2000*



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Contract No. DE-AC36-99-GO10337

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# A Low-Cost Approach to Fabrication of Multinary Compounds for Energy-Related Applications

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Non-vacuum electrodeposition and electroless deposition techniques with a potential to prepare large-area uniform precursor films using low-cost source materials and low-cost capital equipment are very attractive for the growth of compound materials for superconductors and photovoltaic applications. In the first part, a low-cost electrodeposition (ED) method will be discussed for fabrication of high-temperature Tl-oxide-based superconductors. In the second part, electrodeposition and electroless deposition of semiconductor Cu-In-Ga-Se thin films will be discussed.

KEYWORDS: low-cost fabrication; multinary compounds; electrodeposition, electroless deposition; superconductors; photovoltaics

Non-vacuum electrodeposition and electroless deposition techniques with a potential to prepare large-area uniform precursor films using low-cost source materials and low-cost capital equipment are very attractive for the growth of compound materials for superconductors and photovoltaic applications.

In the first part of the paper, a low-cost electrodeposition (ED) method will be discussed for fabricating high-temperature Tl-oxide-based superconductors. The primary technical challenge that must be satisfied to permit high-temperature superconductor (HTS) wire or tape in superconducting magnets or power-related applications is the successful demonstration of a low-cost, high-field, high-current-carrying wire or tape with acceptable mechanical properties ( $>10^5$  A/cm<sup>2</sup> at 77 K in magnetic fields of  $>0.2$  T). The Tl-based superconducting oxides are excellent candidates because of their high transition temperatures reaching to 127 K and unique features in their growth morphology. Research on the single-layer Tl-1223 compound, with Pb, Bi, and Sr substitution for the Tl and Ba, respectively, has recently received more attention due to the promise of improved transport behavior in magnetic field and phase stability competitive with the YBa<sub>2</sub>Cu<sub>3</sub>O<sub>x</sub> (YBCO) compound at 77 K operating temperature.<sup>1,2</sup> Electrodeposited (Tl,Bi)-(Sr,Ba)-Ca-Cu-Ag (TBSBCCO) thick-film wire or tape has considerable practical potential for fabricating a low-cost, high-field, high-current-carrying conductor suitable for superconducting magnets or power-

related applications. A multi-cation thick coating of 1-5  $\mu$ m can be electrodeposited easily at the desired stoichiometry from an electrolyte solution onto a conducting substrate. At present, we are optimizing a low-cost, commercially scalable ED processing to demonstrate biaxially textured Tl-1223 with Bi and Sr substitution on single-crystal substrates that will be transitioned to the flexible textured Ni.<sup>3</sup> The single-crystal results will establish a base-line reference and proof of principle for transition to a suitably buffered metallic substrate. The electrodeposited superconductor precursor films were obtained by co-electrodeposition of the constituent metals using nitrate salts dissolved in dimethyl sulfoxide (DMSO) solvent. The electrodeposition was performed in a closed-cell configuration at 24°C. A number of electrodeposition runs were performed with different electrolyte compositions, and the precursor films were analyzed by inductively coupled plasma (ICP) spectrometry to establish the stoichiometry of the deposited elements. The cation ratios of the electrodeposition bath were adjusted systematically to obtain (TlBi)<sub>0.9</sub>Sr<sub>1.6</sub>Ba<sub>0.4</sub>Ca<sub>2</sub>Cu<sub>3</sub>Ag<sub>0.2</sub> (TBSBCCO-Ag) precursor compositions. A typical electrolyte bath composition for the TBSBCCO-Ag films consisted of 0.018 M TlNO<sub>3</sub>, 0.009 M Bi(NO<sub>3</sub>)<sub>3</sub>·5H<sub>2</sub>O, 0.297 M Sr(NO<sub>3</sub>)<sub>2</sub>, 0.212 M Cu(NO<sub>3</sub>)<sub>2</sub>·6H<sub>2</sub>O, and 0.002 M AgNO<sub>3</sub> dissolved in dimethyl sulfoxide solvent. The films were electroplated by using constant potential at -3 V. Pole-figure measurements of electrodeposited (TBSBCCO) films, with thicknesses between 1-5  $\mu$ m, clearly show strong biaxial texturing. The rocking curve and phi scan of TBSBCCO on 300-Å Ag/LaAlO<sub>3</sub> show a full-width half-maximum (FWHM) of only 0.52° and 0.5°, respectively, consistent with a very high-quality film. Transport measurements for the ED films show critical current density  $J_c$  values above  $10^6$  A/cm<sup>2</sup> at 77 K in zero magnetic field (Fig.1). The criterion for the critical current density ( $J_c$ ) measurements was 1  $\mu$ V/cm electric field. The magnetic field was applied parallel to the c plane of the superconductor (H//c). The  $J_c$  value of ED Tl-1223 films are comparable to the highest value ever reported for any processing technique, including pulsed-laser deposition, sputtering, and e-beam techniques.<sup>4-6</sup>

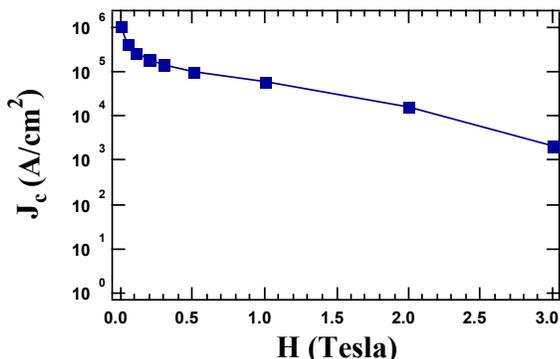


Fig. 1. The magnetic-field dependence of transports  $J_c$  at 77 K (H//c) of an ED-TBSBCCO-Ag film on LAO

In the second part of the paper, electrodeposition and electroless deposition of semiconductor Cu-In-Ga-Se thin films are discussed. Thin-film  $\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2$  (CIGS)-based solar cells have the highest performance efficiencies in both small-area devices and large-area ( $4000 \text{ cm}^2$ ) modules: 18.8%<sup>7</sup> and 12.1%,<sup>8</sup> respectively. Test modules and arrays based on CIGS-based devices have been operating outdoors for more than 10 years with little degradation.<sup>9</sup> The 18.8%-efficient device prepared in our research laboratory<sup>7</sup> is based on a multistep process using physical vapor deposition (PVD). The PVD technique is challenging to scale up because of film non-uniformity and low material utilization. Sputtering techniques are suitable for large-area deposition; however, they require expensive vacuum equipment and sputtering targets. Therefore, non-

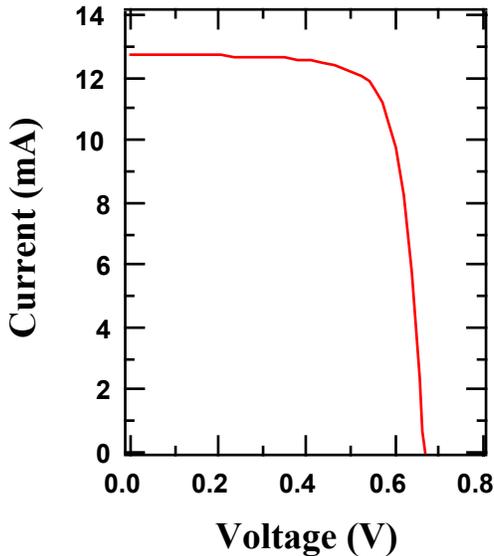


Fig. 2. I-V characteristics of an ED device ( $V_{oc} = 0.666 \text{ V}$ ,  $I_{sc} = 12.76 \text{ mA}$ ,  $J_{sc} = 30.51 \text{ mA/cm}^2$  Fill Factor = 75.56%, Efficiency = 15.4%).

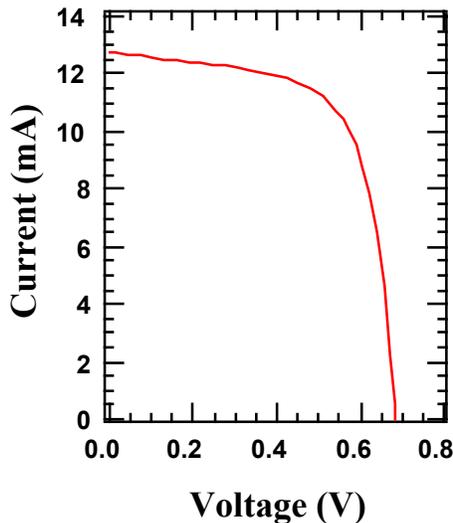


Fig. 3. I-V characteristics of an EL device ( $V_{oc} = 0.6866 \text{ V}$ ,  $I_{sc} = 12.72 \text{ mA}$ ,  $J_{sc} = 29.29 \text{ mA/cm}^2$ , Fill Factor = 66.87%, Efficiency = 13.4%).

vacuum electrodeposition and electroless deposition (EL) techniques<sup>10,11</sup> with a potential to prepare large-area uniform precursor films using low-cost source materials and low-cost capital equipment are very attractive for the growth of CIGS layers for photovoltaic applications. We have fabricated 15.4%-efficient (Fig.2) and 13.4%-efficient (Fig.3)

$\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2$  (CIGS)-based devices from electrodeposited and electroless-deposited precursors. As-deposited precursors are Cu-rich films and polycrystalline or amorphous in nature. Additional In, Ga, and Se were added to the precursor films by physical evaporation to adjust the final composition to  $\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2$ . Addition of In and Ga and also selenization at high temperature are crucial to obtain high-efficiency devices. The films/devices have been characterized by ICP spectrometry, Auger electron spectroscopy, X-ray diffraction, electron-probe microanalysis, current-voltage (I-V) characteristics, and spectral response.

The ED and EL deposition processes are simple and fast, and they can synthesize multi-component precursors for subsequent processing into high-quality multinary compounds for energy-related applications.

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REPORT DOCUMENTATION PAGE			Form Approved OMB NO. 0704-0188	
Public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden, to Washington Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington, VA 22202-4302, and to the Office of Management and Budget, Paperwork Reduction Project (0704-0188), Washington, DC 20503.				
1. AGENCY USE ONLY (Leave blank)		2. REPORT DATE December 1999	3. REPORT TYPE AND DATES COVERED Conference Paper	
4. TITLE AND SUBTITLE A Low-Cost Approach to Fabrication of Multinary Compounds for Energy-Related Applications			5. FUNDING NUMBERS	
6. AUTHOR(S) Raghu N. Bhattacharya and Satyen K. Deb			C TA: PV001501	
7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES)			8. PERFORMING ORGANIZATION REPORT NUMBER	
9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES) National Renewable Energy Laboratory 1617 Cole Blvd. Golden, CO 80401-3393			10. SPONSORING/MONITORING AGENCY REPORT NUMBER CP-590-27518	
11. SUPPLEMENTARY NOTES				
12a. DISTRIBUTION/AVAILABILITY STATEMENT National Technical Information Service U.S. Department of Commerce 5285 Port Royal Road Springfield, VA 22161			12b. DISTRIBUTION CODE	
13. ABSTRACT ( <i>Maximum 200 words</i> ) Non-vacuum electrodeposition and electroless deposition techniques with a potential to prepare large-area uniform precursor films using low-cost source materials and low-cost capital equipment are very attractive for the growth of compound materials for superconductors and photovoltaic applications. In the first part, a low-cost electrodeposition (ED) method will be discussed for fabrication of high-temperature Tl-oxide-based superconductors. In the second part, electrodeposition and electroless deposition of semiconductor Cu-In-Ga-Se thin films will be discussed.				
14. SUBJECT TERMS low-cost fabrication; multinary compounds; electrodeposition, electroless deposition; superconductors; photovoltaics			15. NUMBER OF PAGES	
			16. PRICE CODE	
17. SECURITY CLASSIFICATION OF REPORT Unclassified	18. SECURITY CLASSIFICATION OF THIS PAGE Unclassified	19. SECURITY CLASSIFICATION OF ABSTRACT Unclassified	20. LIMITATION OF ABSTRACT UL	